Spread Spectrum Clock Generator MB88153A

MB88153A-100/101/110/111

■ DESCRIPTION

MB88153A is a clock generator for EMI (Electro Magnetic Interference) reduction. The peak of unnecessary (EMI) can be attenuated by making the oscillation frequency slightly modulate periodically with the internal modulator. It corresponds to both of the center spread which modulates input frequency as Middle Centered and down spread which modulates so as not to exceed input frequency.

■ FEATURE

- Power down pin : 10 μA (Typ-sample) consumption current at power down
- Input frequency: 16.6 MHz to 134 MHz
- Output frequency: 16.6 MHz to 134 MHz (One-fold input frequency)
- Modulation rate can select from \pm 0.5%, \pm 1.5% 1.0% or 3.0%. (For center spread / down spread.)
- Modulation clock output Duty: 40% to 60%
- Modulation clock Cycle-Cycle Jitter: Less than 100 ps
- Low current consumption by CMOS process : 4.0 mA (24 MHz : Typ-sample, no load)
- Power supply voltage : 3.3 V \pm 0.3 V
- Operating temperature : − 40 °C to +85 °C
- Package: 8-pin SOP

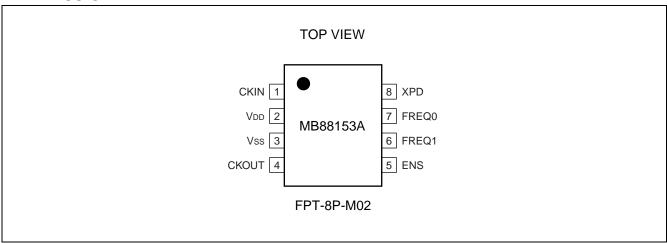


■ PRODUCT LINEUP

MB88153A has four kinds of modulation rate and modulation type (center spread/down spread).

Product	Modulation rate	Modulation type
MB88153A-100	-1.0%	Down spread
MB88153A-101	-3.0%	Down spread
MB88153A-110	±0.5%	Center spread
MB88153A-111	±1.5%	Center spread

■ PIN ASSIGNMENT



■ PIN DESCRIPTION

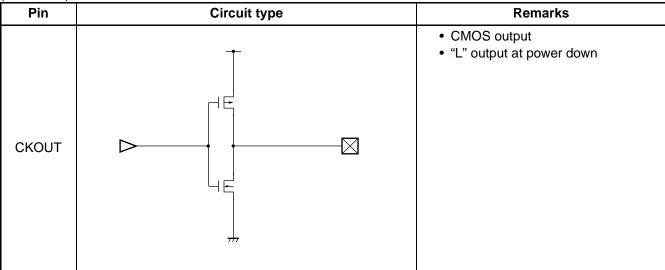
Pin name	I/O	Pin no.	Description
CKIN	I	1	Clock input pin
V _{DD}	_	2	Power supply voltage pin
Vss	_	3	GND pin
CKOUT	0	4	Modulated clock output pin "L" output at power down
ENS	I	5	Modulation enable setting pin
FREQ1	I	6	Frequency setting pin
FREQ0	I	7	Frequency setting pin (with pull-up resistor)
XPD	I	8	Power down pin (with pull-up resistor) Power down at "L" input

■ I/O CIRCUIT TYPE

Pin	Circuit type	Remarks
CKIN, ENS, FREQ1		CMOS hysteresis input
FREQ0	50 kΩ	CMOS hysteresis input with pull-up resistor 50 kΩ (Typ)
XPD	50 kΩ 800 kΩ	CMOS hysteresis input with 50 k Ω + 800 k Ω (Typ) pull-up resistors Note: If "L" is input to XPD when the XPD function is selected, 50 k Ω pull-up resistor is disconnected.

(Continued)

(Continued)



■ HANDLING DEVICES

Preventing Latch-up

A latch-up can occur if, on this device, (a) a voltage higher than V_{DD} or a voltage lower than V_{SS} is applied to an input or output pin or (b) a voltage higher than the rating is applied between V_{DD} pin and V_{SS} pin. The latch-up, if it occurs, significantly increases the power supply current and may cause thermal destruction of an element. When you use this device, be very careful not to exceed the maximum rating.

Handling unused pins

Do not leave an unused input pin open, since it may cause a malfunction. Handle by, using a pull-up or pull-down resistor.

Unused output pin should be opened.

Power supply pins

Please design connecting the power supply pin of this device by as low impedance as possible from the current supply source.

We recommend connecting electrolytic capacitor (about 10 μ F) and the ceramic capacitor (about 0.01 μ F) in parallel between Vss pin and VDD pin near the device, as a bypass capacitor.

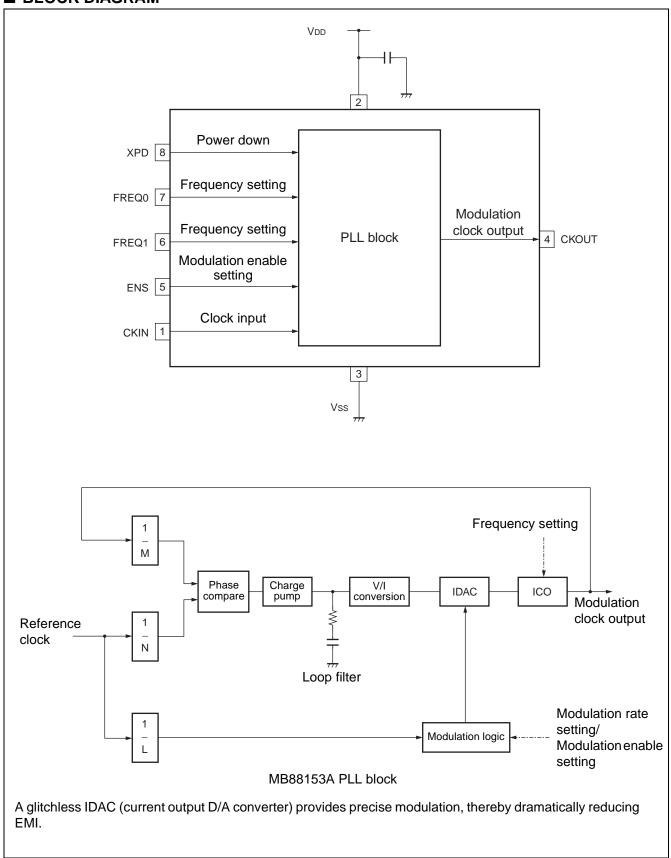
Clock I/O circuit

Noise near the CKIN pin may cause the device to malfunction. Design the printed circuit board so that the wiring for the clock input does not intersect any other wiring.

Please pay attention so that an overshoot and an undershoot do not occur to an input clock of CKIN pin.

Design the printed circuit board that surrounds the CKIN and CKOUT pins with ground.

■ BLOCK DIAGRAM



■ PIN SETTING

When changing the pin setting, the stabilization wait time for the modulation clock required. The stabilization wait time for the modulation clock takes the maximum value of Lock-Up time in "■ ELECTRICAL CHARACTER-ISTICS • AC Characteristics".

ENS modulation enable setting

ENS	Modulation
L	No modulation
Н	Modulation

Note: Spectrum does not spread when "L" is set to ENS. The clock with low jitter can be obtained.

FREQ0, FREQ1 frequency setting

FREQ0	FREQ1	Input frequency range
L	L	16.6 MHz to 40 MHz
L	Н	66 MHz to 134 MHz
Н	L	33 MHz to 67 MHz
Н	Н	40 MHz to 80 MHz

Note: It is set according to the frequency of the clock input to the device. Set FREQ0 pin to "H" for the pin opened because FREQ0 pin has pull-up resistor.

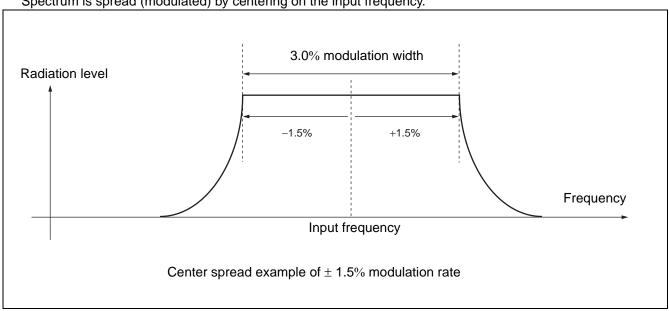
XPD power down setting

XPD	Power down
L	Power down
Н	Normal operation

Note: When "L" is set to XPD pin, the power down operation is implemented and "L" is output to CKOUT pin. When "H" is input to XPD pin or XPD pin is opened, normal operation is implemented because the XPD pin has pull-up resistor.

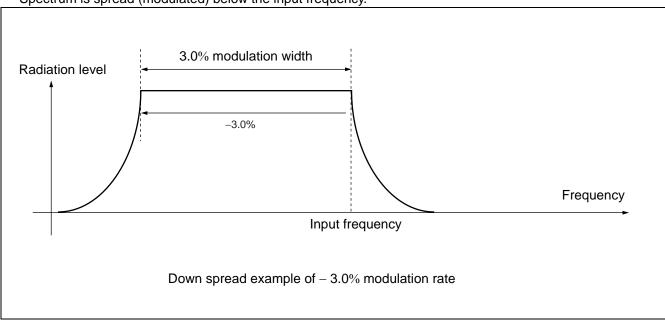
• Center spread

Spectrum is spread (modulated) by centering on the input frequency.



• Down spread

Spectrum is spread (modulated) below the input frequency.

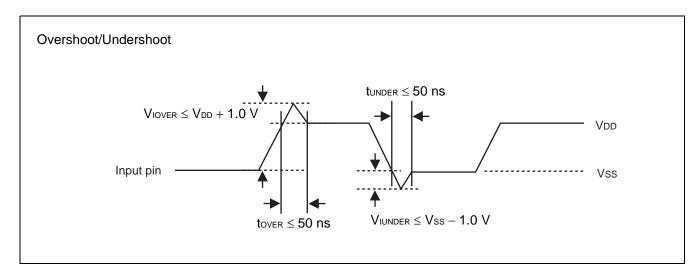


■ ABSOLUTE MAXIMUM RATINGS

Parameter	Cumbal	Rating				
Parameter	Symbol	Min	Max	- Unit		
Power supply voltage*	V _{DD}	- 0.5	+ 4.0	V		
Input voltage*	Vı	Vss - 0.5	V _{DD} + 0.5	V		
Output voltage*	Vo	Vss - 0.5	V _{DD} + 0.5	V		
Storage temperature	Тѕт	– 55	+ 125	°C		
Operation junction temperature	TJ	- 40	+ 125	°C		
Output current	lo	- 14	+ 14	mA		
Overshoot	VIOVER	_	$V_{DD} + 1.0 \text{ (tover} \le 50 \text{ ns)}$	V		
Undershoot	Viunder	$Vss - 1.0$ (tunder ≤ 50 ns)	_	V		

^{* :} The parameter is based on Vss = 0.0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.



■ RECOMMENDED OPERATING CONDITIONS

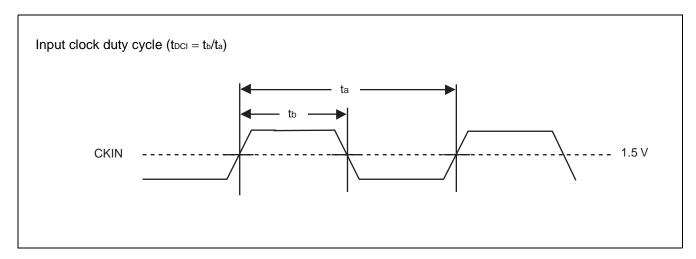
(Vss = 0.0 V)

Parameter	Sym-	Pin	Conditions		Unit		
rarameter	bol	FIII	Conditions	Min	Тур	Max	Oilit
Power supply voltage	V _{DD}	V _{DD}	_	3.0	3.3	3.6	V
"H" level input voltage	VıH	CKIN, ENS, FREQ0, FREQ1, XPD	_	V _{DD} × 0.8	_	V _{DD} + 0.3	V
"L" level input voltage	Vıl	CKIN, ENS, FREQ0, FREQ1, XPD		Vss		V _{DD} × 0.2	V
Input clock duty cycle	tocı	CKIN	16.6 MHz to 134 MHz	40	50	60	%
Operating temperature	Ta	_		- 40		+ 85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.



■ ELECTRICAL CHARACTERISTICS

• DC Characteristics

(Ta =
$$-$$
 40 °C to $\,+$ 85 °C, V_DD = 3.3 V \pm 0.3 V, Vss = 0.0 V)

Parameter	Symbol	Pin	Conditions		Value		Unit	
raiametei	Syllibol	FIII	Conditions	Min	Тур	Max	Onit	
Output voltage	Vон	СКОИТ	"H" level output Іон = - 4 mA	V _{DD} - 0.5	_	V _{DD}	V	
Output voltage	Vol	СКОИТ	"L" level output IoL = 4 mA	Vss	_	0.4	V	
Output impedance	Zo	CKOUT	16.6 MHz to 134 MHz	_	45		Ω	
Input capacitance	Cin	-	$Ta = +25 ^{\circ}C,$ $V_{DD} = V_{I} = 0.0 V,$ f = 1 MHz	_		16	pF	
			16.6 MHz to 67 MHz	_	_	15		
Load capacitance	CL	CKOUT	67 MHz to 100 MHz	_		10	pF	
			100 MHz to 134 MHz	_		7		
Input Dull up registence	Rpue	FREQ0	V _{IL} = 0.0 V	25	50	200	1.0	
Input Pull-up resistance	Rpup	XPD	VIL = 0.0 V	500	800	1200	- kΩ	
Power supply current	Icc	V _{DD}	No load capacitance at 24 MHz output	_	4.0	6.0	mA	
Power down current	lpd	V _{DD}	Input clock stopping	_	10	—	μА	

• AC Characteristics

(Ta =
$$-40$$
 °C to $+85$ °C, V_{DD} = 3.3 V \pm 0.3 V, Vss = 0.0 V)

Parameter	Symbol	Din	Symbol Pin Conditions		Value		
Farameter	Syllibol	PIII	Conditions	Min	Тур	Max	Unit
Input frequency	fin	CKIN	_	16.6	_	134	MHz
Output frequency	fоит	CKOUT	_	16.6	_	134	MHz
Output slew rate	SR	СКОИТ	Load capacitance 15 pF 0.4 V to 2.4 V	0.4		4.0	V/ns
Output clock duty cycle	tocc	CKOUT	1.5 V	40	_	60	%
	fмор (nмор) СКОUТ	CKOLIT	FREQ[1:0] = (00)	fin/2640 (2640)	fin/2280 (2280)	fin/1920 (1920)	
Modulation frequency (Number of input clocks			FREQ[1:0] = (10)	fin/4400 (4400)	fin/3800 (3800)	fin/3200 (3200)	kHz
per modulation)		CROOT	FREQ[1:0] = (11)	fin/5280 (5280)	fin/4560 (4560)	fin/3840 (3840)	(clks)
			FREQ[1:0] = (01)	fin/8800 (8800)	fin/7600 (7600)	fin/6400 (6400)	

(Continued)

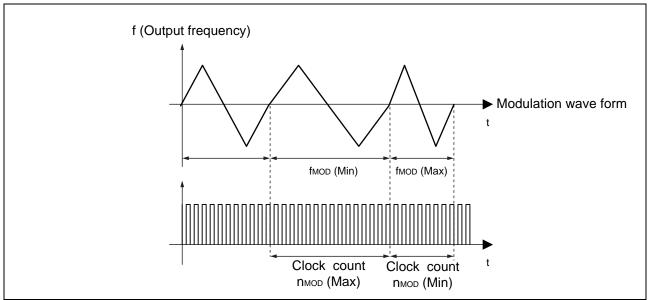
(Continued)

$$(Ta = -40 \, ^{\circ}C \text{ to } + 85 \, ^{\circ}C, \, V_{DD} = 3.3 \, V \pm 0.3 \, V, \, V_{SS} = 0.0 \, V)$$

Parameter	Symbol	Pin	Conditions	Value			l loit
	Symbol		Conditions	Min	Тур	Max	Unit
Look up timo	4	CKOUT	16.6 MHz to 80 MHz		2	5	ma
Lock-up time	t LK	CKOUT	80 MHz to 134 MHz	_	3	8	ms
Cycle-cycle jitter	tuc	CKOUT	No load capacitance, $Ta = +25 ^{\circ}C$, $V_{DD} = 3.3 ^{\circ}V$	_	_	100	ps-rms

Note: The modulation clock stabilization wait time is required after the power is turned on, the IC recovers from power saving, or after FREQ (frequency range) or ENS (modulation ON/OFF) setting is changed. For the modulation clock stabilization wait time, assign the maximum value for lock-up time.

Definition of modulation frequency and number of input clocks per modulation>

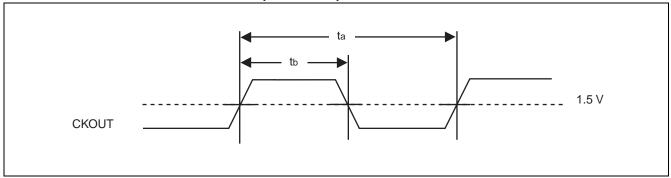


MB88153A contains the modulation period to realize the efficient EMI reduction.

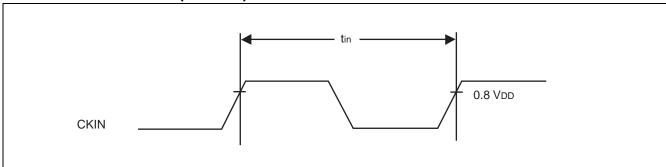
The modulation period fmod depends on the input frequency and changes between fmod (Min) and fmod (Max).

Furthermore, the average value of fmod equals the typical value of the electrical characteristics.

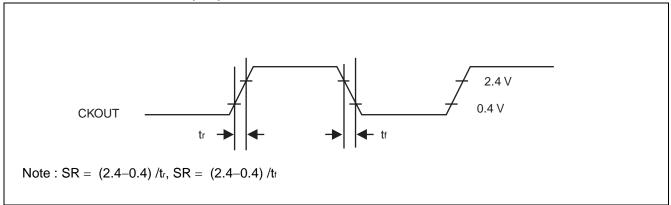
■ OUTPUT CLOCK DUTY CYCLE (tDCC = tb/ta)



■ INPUT FREQUENCY (fin = 1/tin)



■ OUTPUT SLEW RATE (SR)



■ CYCLE-CYCLE JITTER

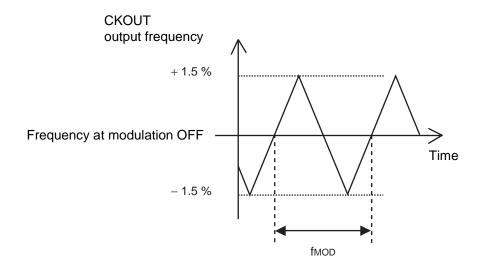


Note: Cycle-cycle jitter is defined the difference between a certain cycle and immediately after (or, immediately before).

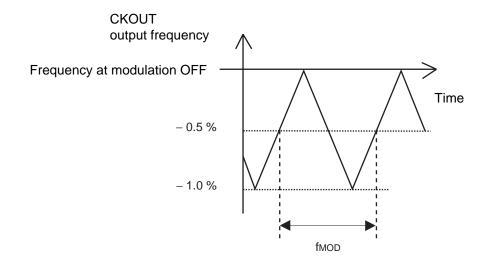
13

■ MODULATION WAVE FORM

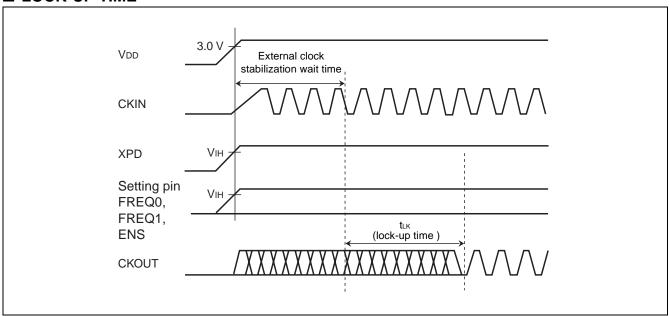
• ±1.5% modulation rate, Example of center spread



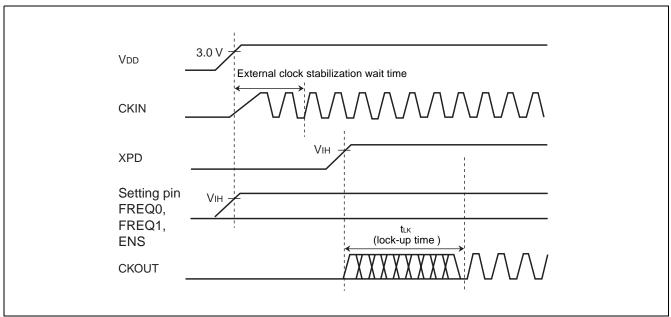
• −1.0% modulation rate, Example of down spread



■ LOCK-UP TIME

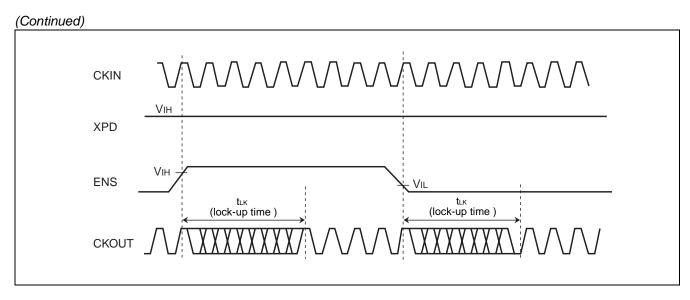


If the XPD pin is fixed at the "H" level, the maximum time after the power is turned on until the set clock signal is output from CKOUT pin is (the stabilization wait time of input clock to CKIN pin) + (the lock-up time "tlk"). For the input clock stabilization time, check the characteristics of the resonator or oscillator used.



When XPD pin controls the power-down, stable clock is output from CKOUT pin after becoming XPD pin = "H" level (in the maximum after lock-Up time (t_{LK})).

(Continued)



When ENS pin is controlled for enable modulation, it is necessary for the stably clock output from CKOUT pin to wait lock-up time (tlk).

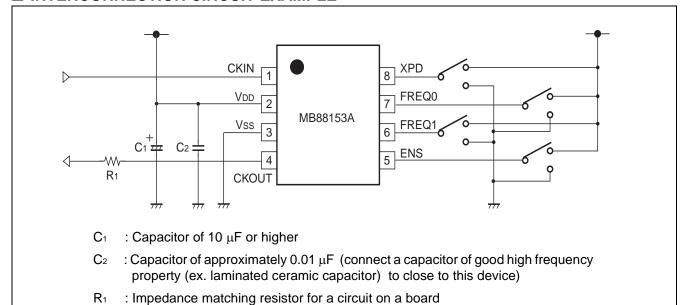
Note: In the following cases, it is necessary for the stably clock output from CKOUT pin, to wait lock-up time (tlk).

- After releasing power-down
- When you change other terminal settings

Output frequency, output clock duty cycle, modulation frequency, and cycle-cycle jitter are not guaranteed until the output clock is stable. It is recommended to take procedure to release of reset after. lock-up time (tlk) on the device using the modulation clock or etc.

■ INTERCONNECTION CIRCUIT EXAMPLE

 R_1

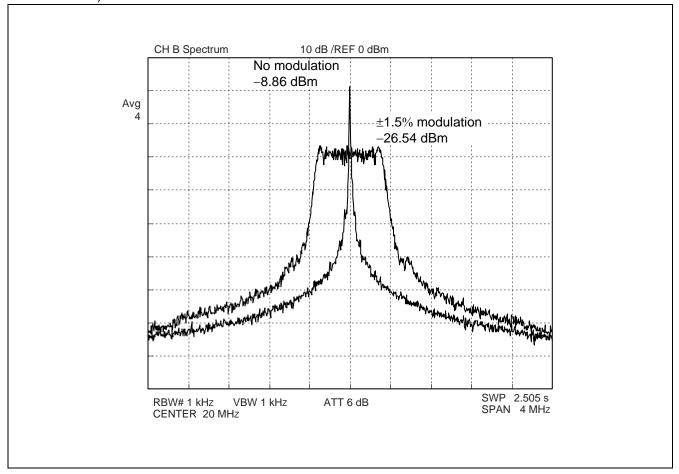


■ SPECTRUM EXAMPLE CHARACTERISTICS

The condition of the examples of the characteristic is shown as follows: Input frequency = 20 MHz (Output frequency = 20 MHz), use for MB88153A-111.

Power-supply voltage = 3.3 V, None load capacity. Modulation rate = \pm 1.5% (center spread).

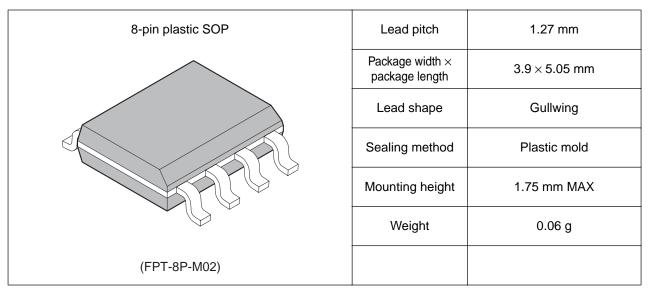
Spectrum analyzer HP4396B is connected with CKOUT. The result of the measurement with RBW = 1 kHz (ATT use for -6 dB).

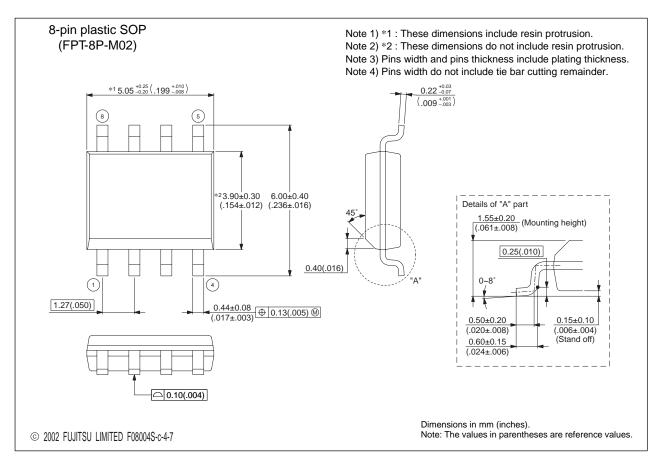


■ ORDERING INFORMATION

Part number	Modulation rate	Modulation type	Package	Remarks
MB88153APNF-G-100-JNE1	-1.0%	Down spread		
MB88153APNF-G-101-JNE1	-3.0%	Down spread	8-pin plastic SOP	
MB88153APNF-G-110-JNE1	±0.5%	Center spread	(FPT-8P-M02)	
MB88153APNF-G-111-JNE1	±1.5%	Center spread		
MB88153APNF-G-100-JNEFE1	-1.0%	Down spread		
MB88153APNF-G-101-JNEFE1	-3.0%	Down spread	8-pin plastic SOP	Emboss taping (EF type)
MB88153APNF-G-110-JNEFE1	±0.5%	Center spread	(FPT-8P-M02)	
MB88153APNF-G-111-JNEFE1	±1.5%	Center spread		
MB88153APNF-G-100-JNERE1	-1.0%	Down spread		
MB88153APNF-G-101-JNERE1	-3.0%	Down spread	8-pin plastic SOP	Emboss taping
MB88153APNF-G-110-JNERE1	±0.5%	Center spread	(FPT-8P-M02)	(ER type)
MB88153APNF-G-111-JNERE1	±1.5%	Center spread		

■ PACKAGE DIMENSION





Please confirm the latest Package dimension by following URL. http://edevice.fujitsu.com/package/en-search/

MEMO		

MEMO		

MEMO		

FUJITSU MICROELECTRONICS LIMITED

Shinjuku Dai-Ichi Seimei Bldg. 7-1, Nishishinjuku 2-chome, Shinjuku-ku, Tokyo 163-0722, Japan Tel: +81-3-5322-3347 Fax: +81-3-5322-3387 http://jp.fujitsu.com/fml/en/

For further information please contact:

North and South America

FUJITSU MICROELECTRONICS AMERICA, INC. 1250 E. Arques Avenue, M/S 333 Sunnyvale, CA 94085-5401, U.S.A. Tel: +1-408-737-5600 Fax: +1-408-737-5999 http://www.fma.fujitsu.com/

Europe

FUJITSU MICROELECTRONICS EUROPE GmbH Pittlerstrasse 47, 63225 Langen, Germany Tel: +49-6103-690-0 Fax: +49-6103-690-122

Tel: +49-6103-690-0 Fax: +49-6103-690-122 http://emea.fujitsu.com/microelectronics/

Korea

FUJITSU MICROELECTRONICS KOREA LTD. 206 KOSMO TOWER, 1002 Daechi-Dong, Kangnam-Gu,Seoul 135-280 Korea

Tel: +82-2-3484-7100 Fax: +82-2-3484-7111

http://www.fmk.fujitsu.com/

Asia Pacific

FUJITSU MICROELECTRONICS ASIA PTE LTD.

151 Lorong Chuan, #05-08 New Tech Park,
Singapore 556741

Tel: +65-6281-0770 Fax: +65-6281-0220

http://www.fujitsu.com/sg/services/micro/semiconductor/

FUJITSU MICROELECTRONICS SHANGHAI CO., LTD. Rm.3102, Bund Center, No.222 Yan An Road(E), Shanghai 200002, China Tel: +86-21-6335-1560 Fax: +86-21-6335-1605 http://cn.fujitsu.com/fmc/

FUJITSU MICROELECTRONICS PACIFIC ASIA LTD.

10/F., World Commerce Centre, 11 Canton Road
Tsimshatsui, Kowloon
Hong Kong
Tel: +852-2377-0226 Fax: +852-2376-3269
http://cn.fujitsu.com/fmc/tw

All Rights Reserved.

The contents of this document are subject to change without notice.

Customers are advised to consult with sales representatives before ordering.

The information, such as descriptions of function and application circuit examples, in this document are presented solely for the purpose of reference to show examples of operations and uses of FUJITSU MICROELECTRONICS device; FUJITSU MICROELECTRONICS does not warrant proper operation of the device with respect to use based on such information. When you develop equipment incorporating the device based on such information, you must assume any responsibility arising out of such use of the information.

FUJITSU MICROELECTRONICS assumes no liability for any damages whatsoever arising out of the use of the information.

Any information in this document, including descriptions of function and schematic diagrams, shall not be construed as license of the use or exercise of any intellectual property right, such as patent right or copyright, or any other right of FUJITSU MICROELECTRONICS or any third party or does FUJITSU MICROELECTRONICS warrant non-infringement of any third-party's intellectual property right or other right by using such information. FUJITSU MICROELECTRONICS assumes no liability for any infringement of the intellectual property rights or other rights of third parties which would result from the use of information contained herein.

The products described in this document are designed, developed and manufactured as contemplated for general use, including without limitation, ordinary industrial use, general office use, personal use, and household use, but are not designed, developed and manufactured as contemplated (1) for use accompanying fatal risks or dangers that, unless extremely high safety is secured, could have a serious effect to the public, and could lead directly to death, personal injury, severe physical damage or other loss (i.e., nuclear reaction control in nuclear facility, aircraft flight control, air traffic control, mass transport control, medical life support system, missile launch control in weapon system), or (2) for use requiring extremely high reliability (i.e., submersible repeater and artificial satellite).

Please note that FUJITSU MICROELECTRONICS will not be liable against you and/or any third party for any claims or damages arising in connection with above-mentioned uses of the products.

Any semiconductor devices have an inherent chance of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of over-current levels and other abnormal operating conditions.

Exportation/release of any products described in this document may require necessary procedures in accordance with the regulations of the Foreign Exchange and Foreign Trade Control Law of Japan and/or US export control laws.

The company names and brand names herein are the trademarks or registered trademarks of their respective owners.